JOC355

Rev.A.1.0

The JOC355 combines an AlGaAs infrared emitting diode as the emitter which is optically coupled to a silicon planar darlington phototransistor detector in a plastic SOP4 package. With the robust coplanar double mold structure, JOC355 provides the most stable isolation feature. The products are widely used in sequence controller telephone/fax, system appliances, measuring instrument and programmable logic controller.

Current transfer ratio CTR: 600%-7500% @I_F=1mA, V_{CE}=2V
High isolation voltage between input and output
(V_{iso}=3,750Vrms)
Operating temperature up to +110°C
Collector-Emitter voltage $BV_{CEO} \geq 40V$
CQC approved
VDE approved
UL approved
The products comply with REACH and HF

(Temperature=25°C)

Parameter		Symbol	Value	Unit
Input	Forward Current	I_F	60	mA
	Peak Forward Current	I_{FP}	1	A
	Reverse Voltage	V_R	6	V
	Power Dissipation	P_D	100	mW
Output	Collector-emitter Voltage	V_{CEO}	40	V

Isolation Voltage	V_{iso}	3750	Vrms
Operating Temperature	T_{opr}	-55~+110	
Storage Temperature	T_{stg}	-55~+	

FIG.7: Normalized Current Transfer Ratio vs. Ambient Temperature

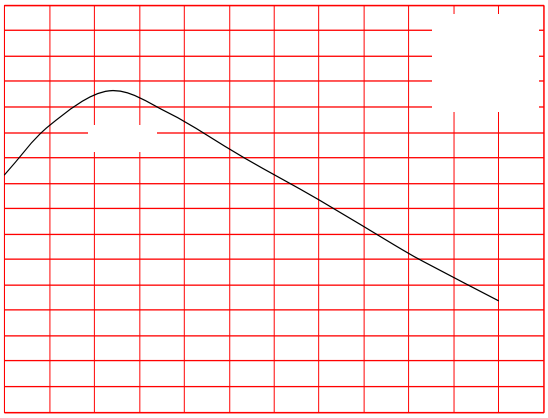


FIG.8: Normalized Collector-emitter Saturation Voltage vs. Ambient Temperature

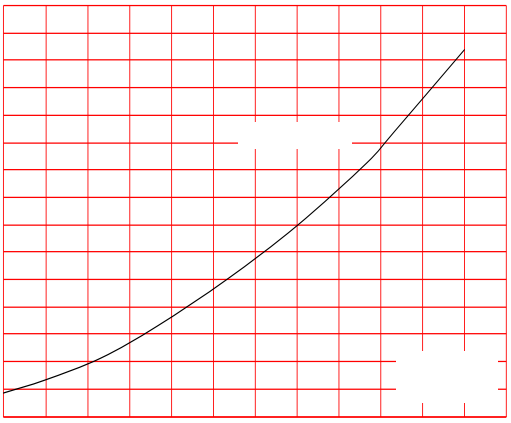


FIG.9: Response Time vs. Load Resistance

FIG.10: Frequency Response

FIG.11: Test Circuits of Response Time

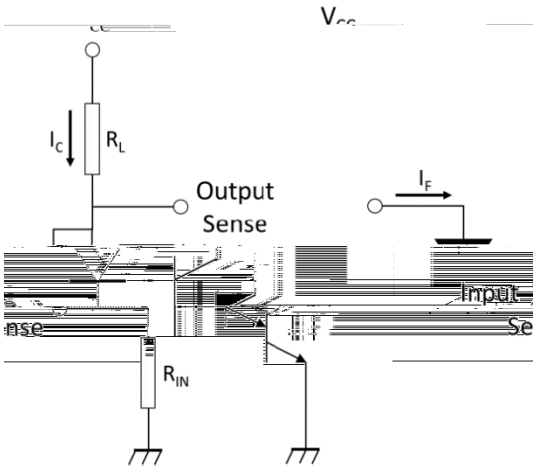


FIG.12: Curves of Response Time

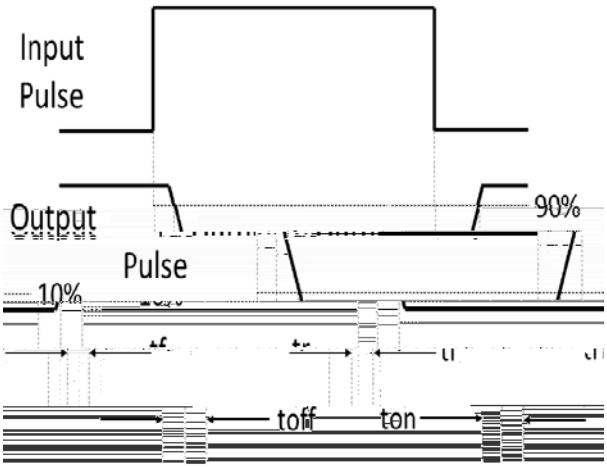
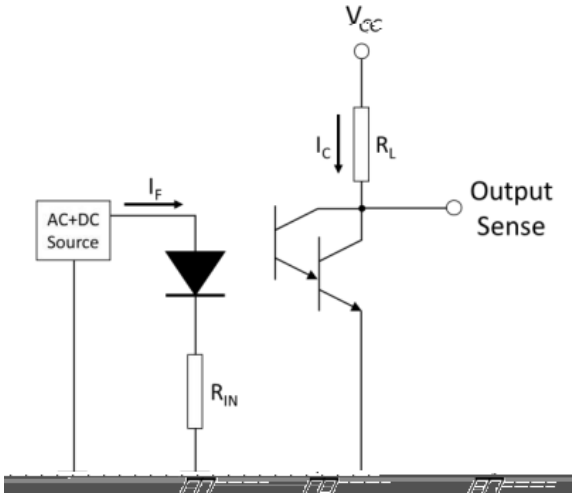
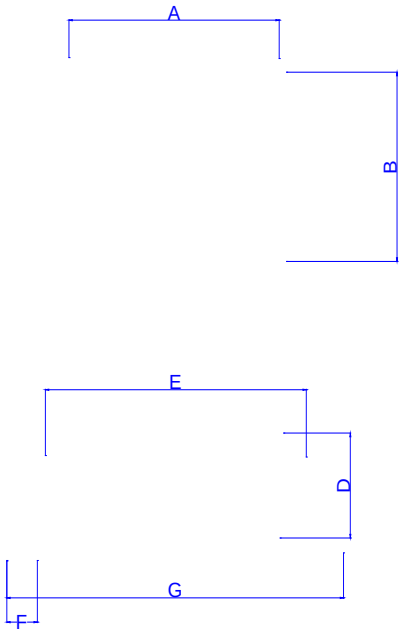


FIG.13: Test Circuits of Frequency Response




A
B
E
D
G
F